



Insulated Gate Bi-Polar Transistor Type T2400GB45E

Absolute Maximum Ratings

| | VOLTAGE RATINGS | MAXIMUM LIMITS | UNITS |
|----------------|--|-----------------------|--------------|
| V_{CES} | Collector – emitter voltage | 4500 | V |
| $V_{DC\ link}$ | Permanent DC voltage for 100 FIT failure rate. | 2800 | V |
| V_{GES} | Peak gate – emitter voltage | ±20 | V |

| | RATINGS | MAXIMUM LIMITS | UNITS |
|-------------|--|-----------------------|--------------|
| I_C | Continuous DC collector current, IGBT | 2400 | A |
| I_{CRM} | Repetitive peak collector current, $t_p=1ms$, IGBT | 4800 | A |
| I_{ECO} | Maximum reverse emitter current, $t_p=100\mu s$, (note 2 & 3) | 2400 | A |
| P_{MAX} | Maximum power dissipation, IGBT (note 2) | 19 | kW |
| $T_{j\ op}$ | Operating temperature range | -40 to +125 | °C |
| T_{stg} | Storage temperature range | -40 to +125 | °C |

Notes: -

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) $T_{sink} = 25^\circ C$, double side cooled.
- 3) Maximum commutation loop inductance 200nH.
- 4) Half-sinewave, $125^\circ C$ T_j initial.

Characteristics

IGBT Characteristics

| | PARAMETER | MIN | TYP | MAX | TEST CONDITIONS | UNITS |
|----------------------|--|-----|------|------|---|-------|
| V _{CE(sat)} | Collector – emitter saturation voltage | - | 2.8 | 3.2 | I _C = 2400A, V _{GE} = 15V, T _j = 25°C | V |
| | | - | 3.6 | 4.0 | I _C = 2400A, V _{GE} = 15V | V |
| V _{T0} | Threshold voltage | - | - | 1.49 | Current range: 800A – 2400A | V |
| r _T | Slope resistance | - | - | 1.05 | | mΩ |
| V _{GE(TH)} | Gate threshold voltage | - | 5.1 | - | V _{CE} = V _{GE} , I _C = 250mA | V |
| I _{CES} | Collector – emitter cut-off current | - | 45 | 70 | V _{CE} = V _{CES} , V _{GE} = 0V | mA |
| I _{GES} | Gate leakage current | - | - | ±30 | V _{GE} = ±20V | μA |
| C _{ies} | Input capacitance | - | 400 | - | V _{CE} = 25V, V _{GE} = 0V, f = 1MHz | nF |
| t _{d(on)} | Turn-on delay time | - | 1.8 | - | I _C = 2400A, V _{CE} = 2800V, di/dt = 4000A/μs V _{GE} = ±15V, L _S = 200nH | μs |
| t _{r(V)} | Rise time | - | 3.6 | - | | μs |
| Q _{g(on)} | Turn-on gate charge | - | 18 | - | R _{G(ON)} = 2.2Ω, R _{G(OFF)} = 8.2Ω, C _{GE} = 267nF | μC |
| E _{on} | Turn-on energy | - | 14 | - | | J |
| t _{d(off)} | Turn-off delay time | - | 5.1 | - | Freewheel diode type E2400EC45E at T _j = 125°C. (Notes 3, 4 & 5) | μs |
| t _{f(I)} | Fall time | - | 2.4 | - | | μs |
| Q _{g(off)} | Turn-off gate charge | - | 14 | - | μC | |
| E _{off} | Turn-off energy | - | 13 | - | J | |
| I _{sc} | Short circuit current | - | 9500 | - | V _{GE} = +15V, V _{CC} = 2800V, V _{CEmax} ≤ V _{CES} , t _p ≤ 10μs | A |

Thermal Characteristics

| | PARAMETER | MIN | TYP | MAX | TEST CONDITIONS | UNITS |
|-------------------|---|-----|-----|------|-----------------------|-------|
| R _{thJK} | Thermal resistance junction to sink, IGBT | - | - | 5.2 | Double side cooled | K/kW |
| | | - | - | 8.5 | Collector side cooled | K/kW |
| | | - | - | 13.5 | Emitter side cooled | K/kW |
| F | Mounting force | 50 | - | 70 | Note 2 | kN |
| W _t | Weight | - | 2 | - | | kg |

Notes:-

- 1) Unless otherwise indicated T_j = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements.
- 3) C_{GE} is additional gate - emitter capacitance added to output of gate drive circuit.
- 4) E_{on} integration time 15μs from 10% rising I_G.
- 5) E_{off} integration time 15μs from 90% falling V_{GE}.
- 6) Freewheeling diode changed from E2400TC45C to E2400EC45E.

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

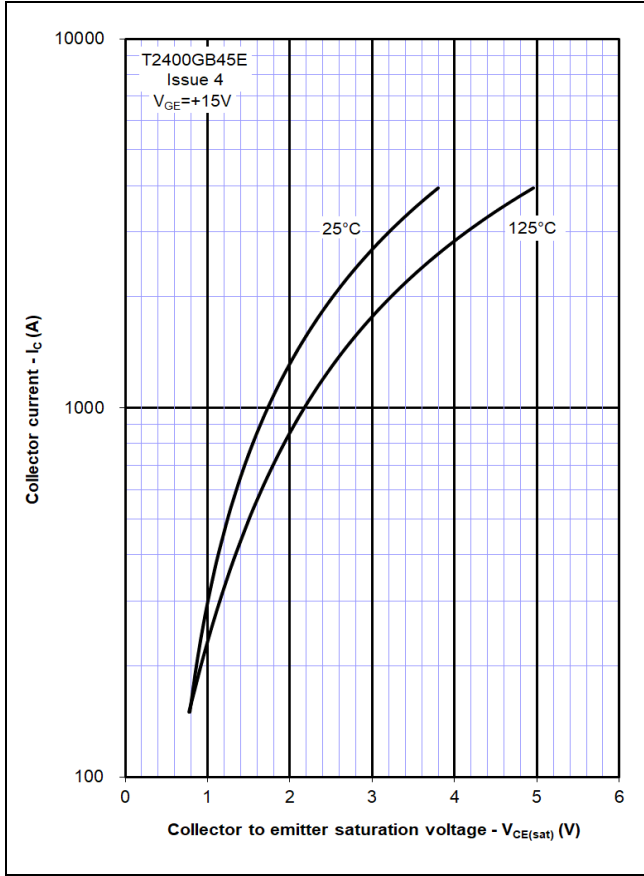


Figure 2 – Typical output characteristic

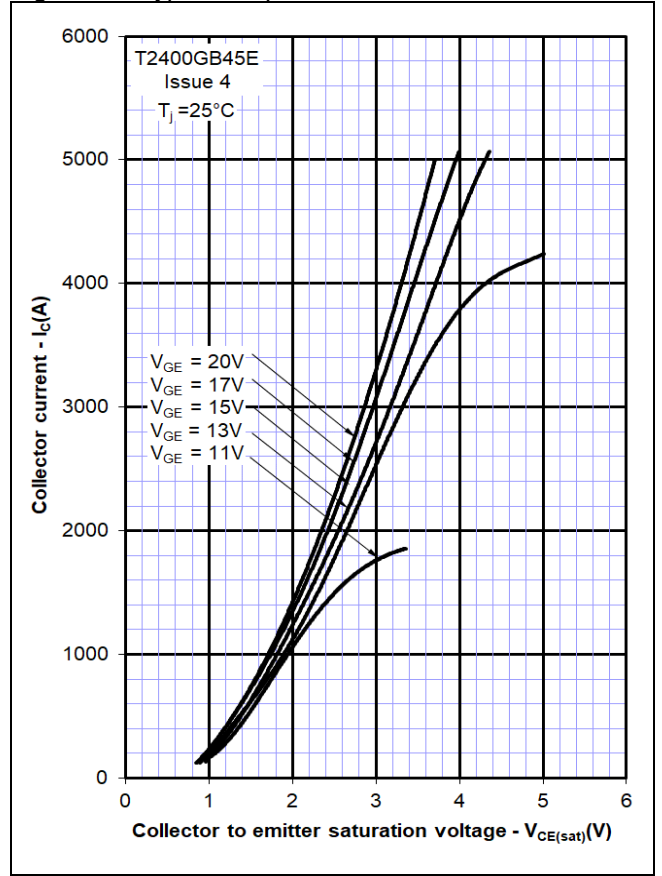


Figure 3 – Typical output characteristic

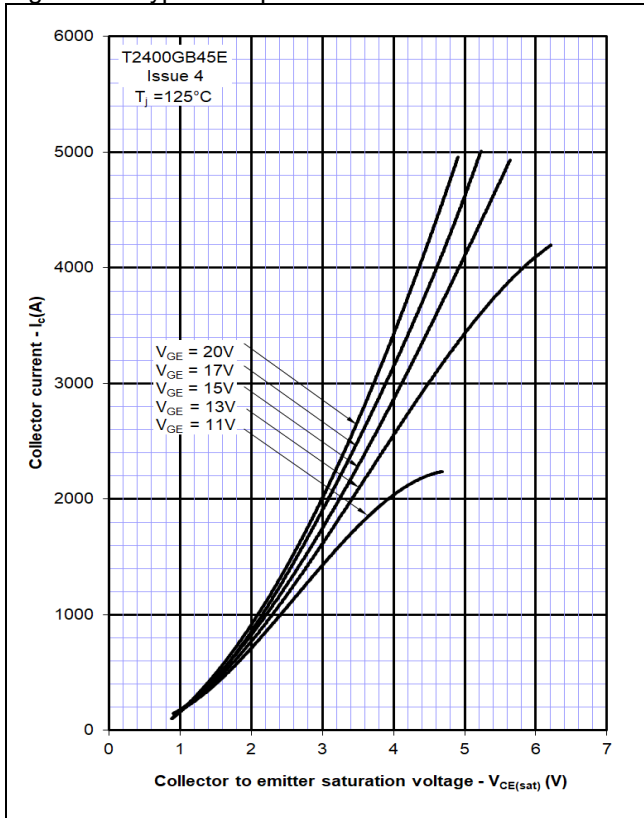


Figure 4 – Typical turn-on delay time vs gate resistance

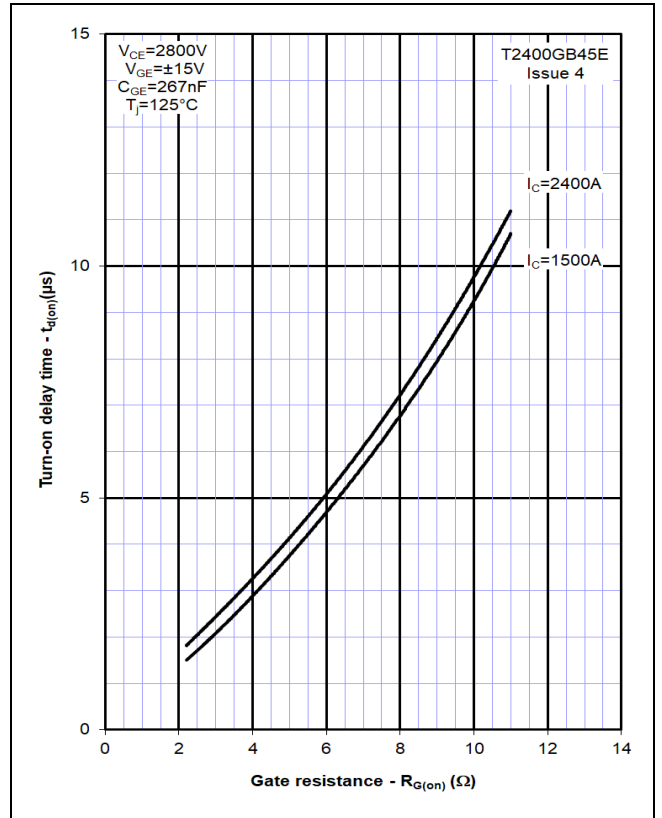


Figure 5 – Typical turn-off delay time vs. gate resistance

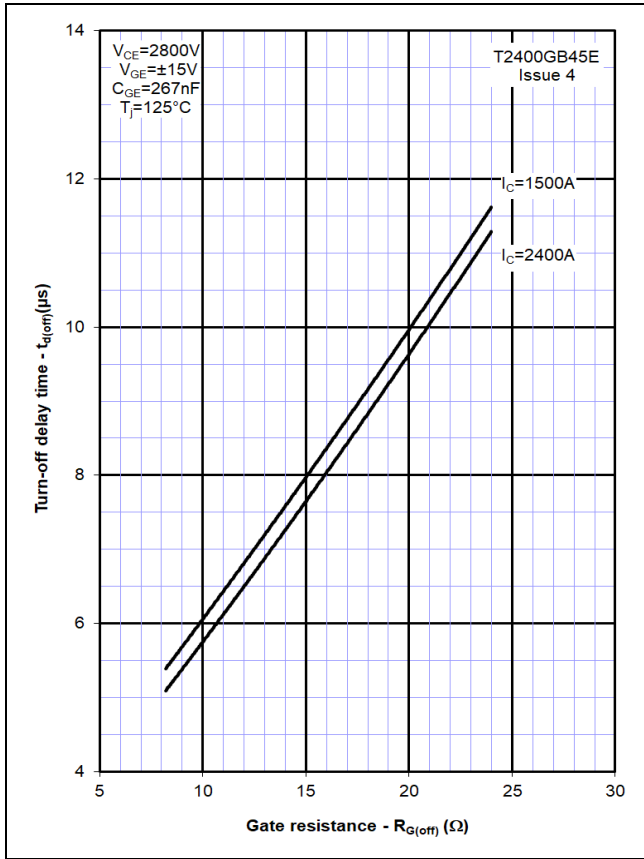


Figure 6 – Typical turn-on energy vs. collector current

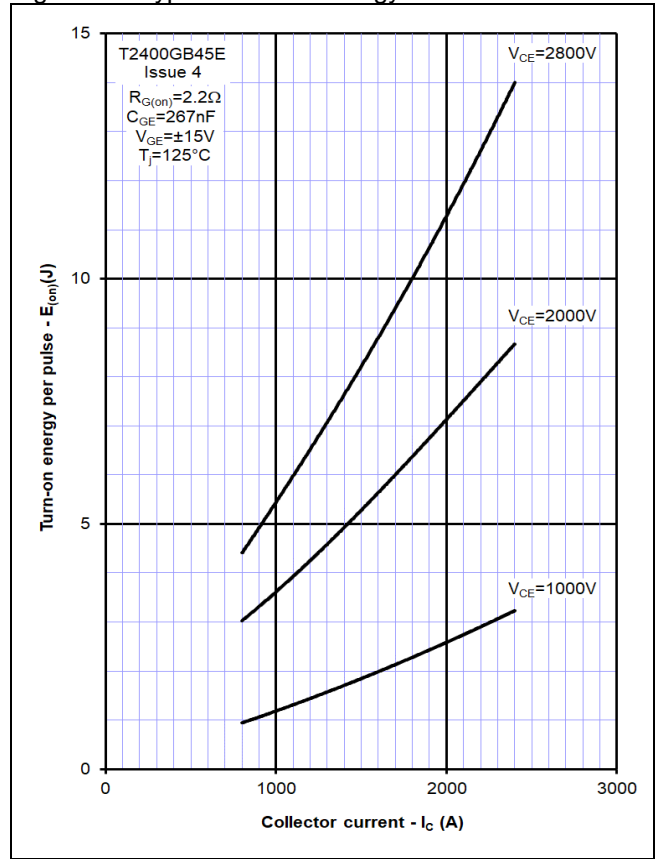


Figure 7 – Typical turn-on energy vs. di/dt

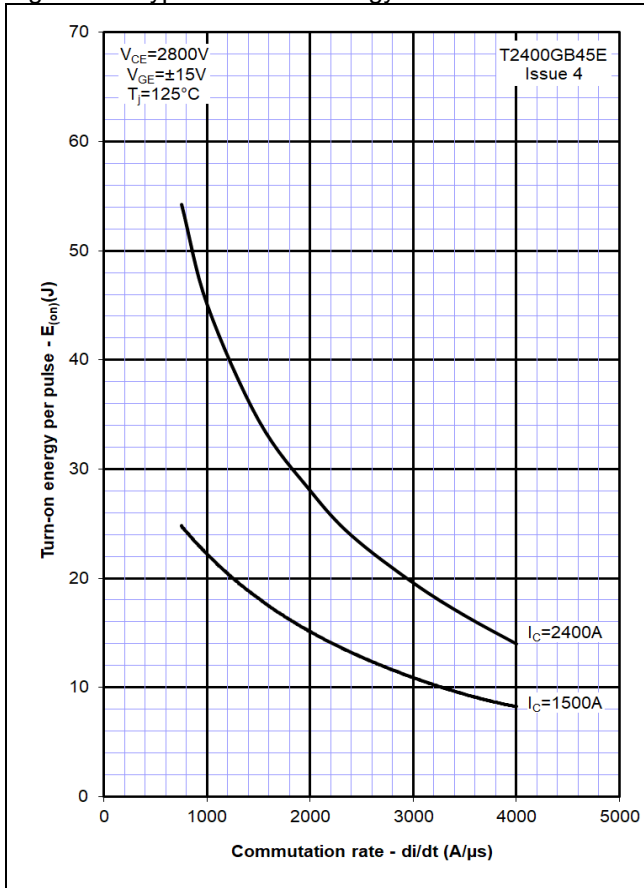


Figure 8 – Typical turn-off energy vs. collector current

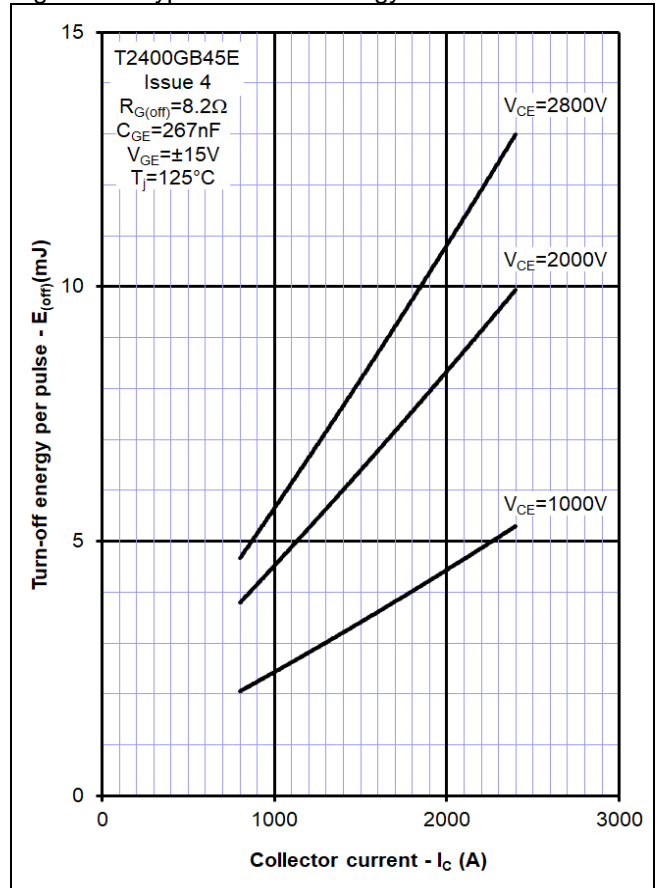


Figure 9 – Turn-off energy vs voltage

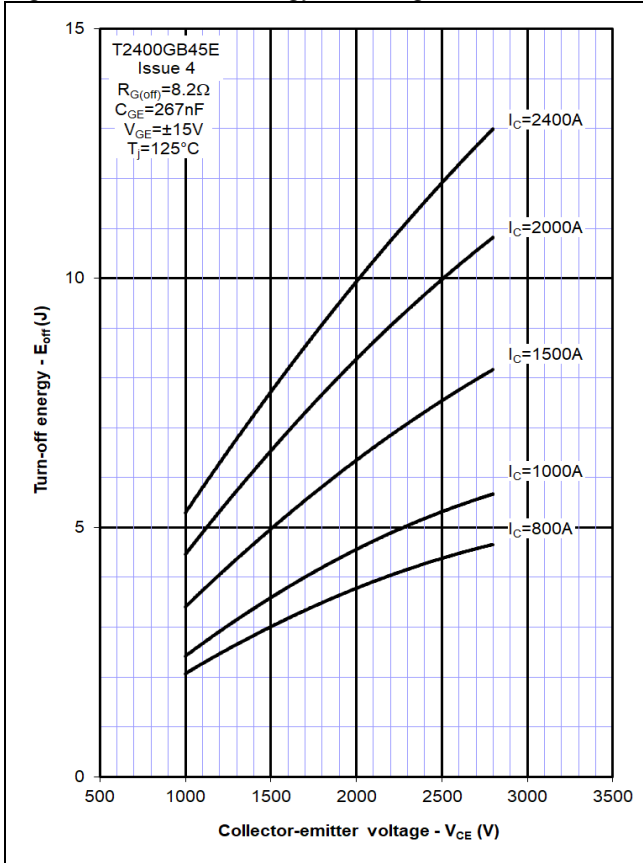


Figure 10 – Safe operating area

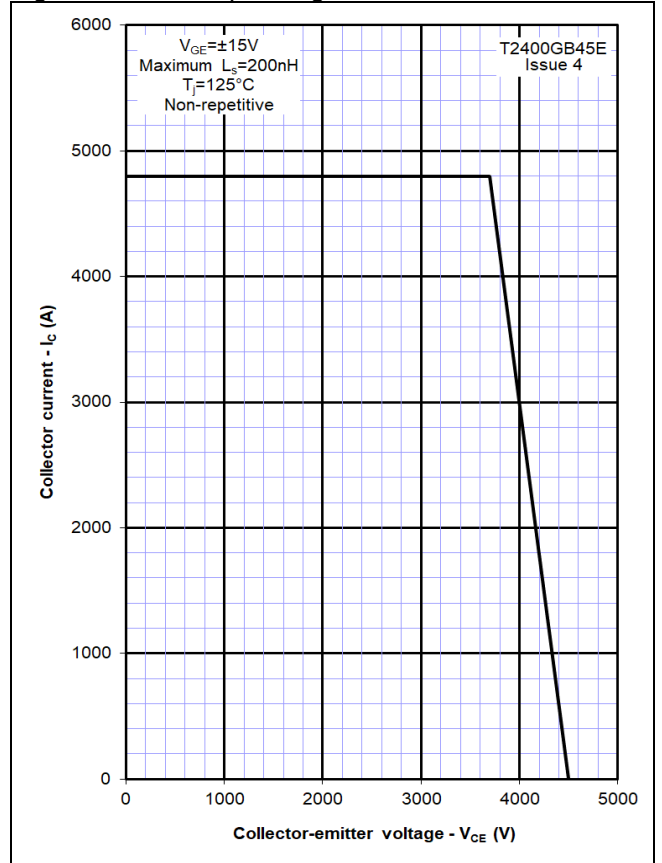
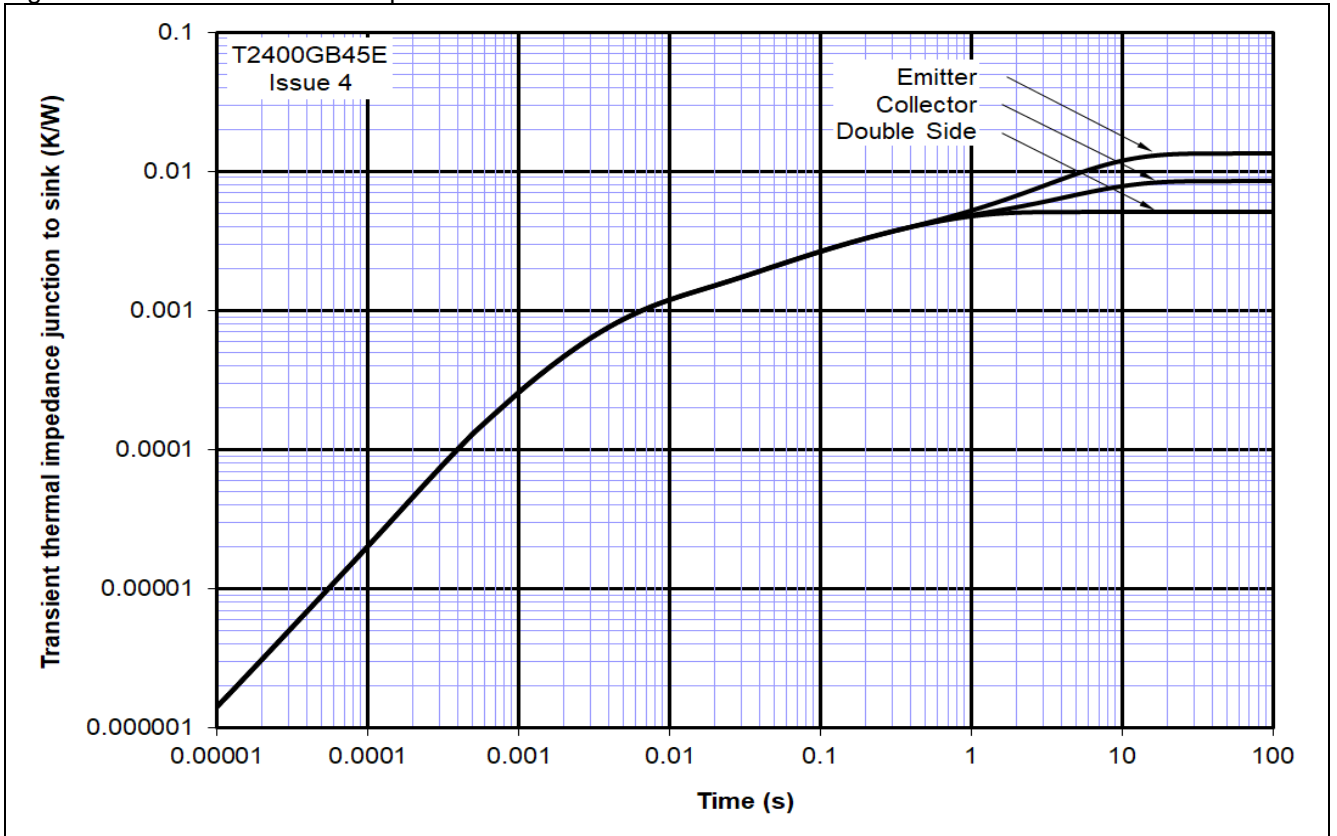
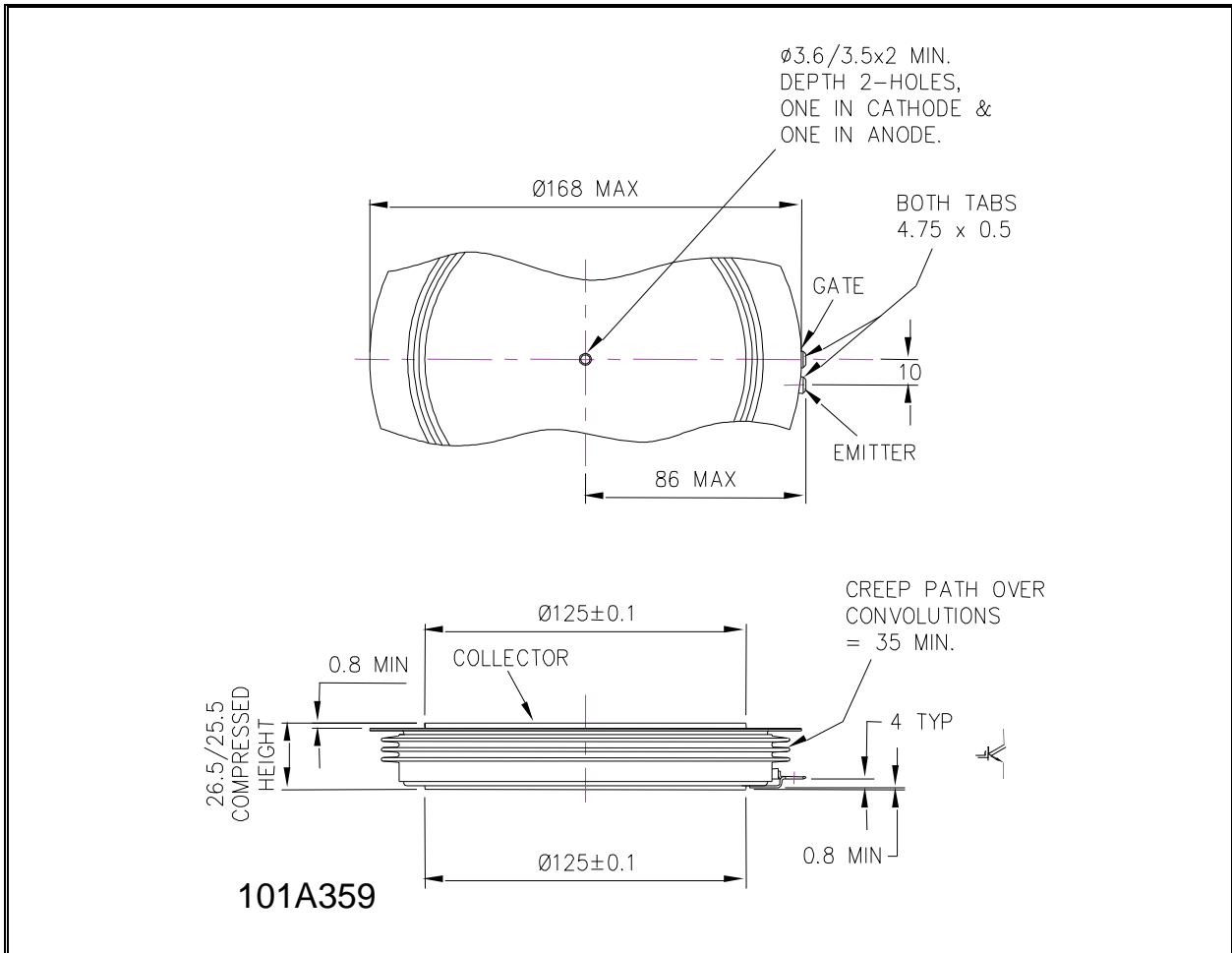


Figure 11 – Transient thermal impedance



Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

| T2400 | GB | 45 | E |
|-----------------|--------------------|--------------------------------------|-------------------|
| Fixed type Code | Fixed Outline Code | Voltage Grade $V_{CES}/100$ 45 | Fixed format code |

 Typical order code: T2400GB45E ($V_{CES} = 4500V$)

IXYS Semiconductor GmbH
 Edisonstraße 15
 D-68623 Lampertheim
 Tel: +49 6206 503-0
 Fax: +49 6206 503-627
 E-mail: marcom@ixys.de



IXYS UK Westcode Ltd
 Langley Park Way, Langley Park,
 Chippenham, Wiltshire, SN15 1GE.
 Tel: +44 (0)1249 444524
 E-mail: sales@ixysuk.com

IXYS Corporation
 1590 Buckeye Drive
 Milpitas CA 95035-7418
 Tel: +1 (408) 457 9000
 Fax: +1 (408) 496 0670
 E-mail: sales@ixys.net

www.littelfuse.com
www.ixysuk.com
www.ixys.net

IXYS Long Beach
 IXYS Long Beach, Inc
 2500 Mira Mar Ave, Long Beach
 CA 90815
 Tel: +1 (562) 296 6584
 Fax: +1 (562) 296 6585
 E-mail: service@ixyslongbeach.com

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